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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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# Digital Transistors (BRT) R1 = 22 k $\Omega$ , R2 = 47 k $\Omega$

# NPN Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### **Features**

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	50	Vdc
Collector Current – Continuous	I <sub>C</sub>	100	mAdc
Input Forward Voltage	$V_{IN(fwd)}$	40	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	8	Vdc

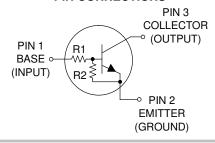
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



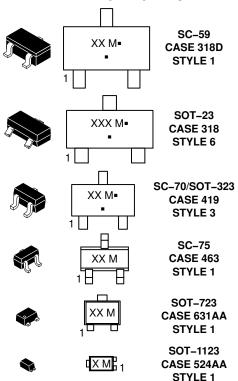
# ON Semiconductor®

#### www.onsemi.com

## **PIN CONNECTIONS**



### **MARKING DIAGRAMS**



XXX = Specific Device Code
M = Date Code\*
Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

### **ORDERING INFORMATION**

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

**Table 1. ORDERING INFORMATION** 

Device	Part Marking	Package	Shipping <sup>†</sup>
MUN2234T1G	8L	SC-59 (Pb-Free)	3000 / Tape & Reel
MMUN2234LT1G, SMMUN2234LT1G*	A8L	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5234T1G, NSVMUN5234T1G*	8L	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTC124XET1G	8L	SC-75 (Pb-Free)	3000 / Tape & Reel
DTC124XM3T5G	8L	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSBC124XF3T5G	J (180°)**	SOT-1123 (Pb-Free)	8000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\* \*</sup> $(xx^\circ)$  = Degree rotation in the clockwise direction.

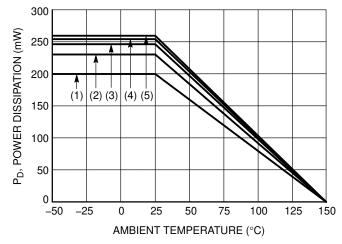


Figure 1. Derating Curve

- (1) SC-75 and SC-70/SOT323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm<sup>2</sup>, 1 oz. copper trace
- (5) SOT-723; Minimum Pad

<sup>\*</sup>S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

**Table 2. THERMAL CHARACTERISTICS** 

Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC-59) (MUN2234)			•	
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	230 338 1.8 2.7	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	540 370	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	264 287	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-23) (MMUN2234L)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	246 400 2.0 3.2	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	508 311	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	174 208	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5234)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	202 310 1.6 2.5	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\thetaJA}$	618 403	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	280 332	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SC-75) (DTC124XE)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	200 300 1.6 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	600 400	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-723) (DTC124XM3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	260 600 2.0 4.8	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	480 205	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

- FR-4 @ Minimum Pad.
   FR-4 @ 1.0 x 1.0 Inch Pad.
   FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
   FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

**Table 2. THERMAL CHARACTERISTICS** 

TODIO E. TITETUMAE OFFATIAO FETIO 1100				
Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-1123) (NSBC123XF3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 3) (Note 4) (Note 3) (Note 4)	P <sub>D</sub>	254 297 2.0 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 3) (Note 4)	$R_{ hetaJA}$	493 421	°C/W
Thermal Resistance, Junction to Lead	(Note 3)	$R_{ hetaJL}$	193	°C/W
Junction and Storage Temperature Range		$T_J,T_stg$	-55 to +150	°C

- 1. FR-4 @ Minimum Pad.
- 2. FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
   FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•	•	•		•
Collector–Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I <sub>CBO</sub>	_	_	100	nAdc
Collector–Emitter Cutoff Current (V <sub>CE</sub> = 50 V, I <sub>B</sub> = 0)	I <sub>CEO</sub>	_	_	500	nAdc
Emitter-Base Cutoff Current (V <sub>EB</sub> = 6.0 V, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	_	0.13	mAdc
Collector–Base Breakdown Voltage ( $I_C = 10 \mu A, I_E = 0$ )	V <sub>(BR)</sub> CBO	50	_	-	Vdc
Collector–Emitter Breakdown Voltage (Note 5) (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	50	_	_	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 5) (I <sub>C</sub> = 5.0 mA, V <sub>CE</sub> = 10 V)	h <sub>FE</sub>	80	150	_	
Collector – Emitter Saturation Voltage (Note 5) (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 1.0 mA)	VCE(sat)	_	_	0.25	Vdc
Input Voltage (off) (V <sub>CE</sub> = 5.0 V, I <sub>C</sub> = 100 $\mu$ A)	$V_{i(off)}$	_	0.9	0.5	Vdc
Input Voltage (on) (V <sub>CE</sub> = 0.3 V, I <sub>C</sub> = 2.0 mA)	V <sub>i(on)</sub>	2.0	1.2	_	Vdc
Output Voltage (on) ( $V_{CC} = 5.0 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1.0 \text{ k}\Omega$ )	V <sub>OL</sub>	_	_	0.2	Vdc
Output Voltage (off) ( $V_{CC} = 5.0 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1.0 \text{ k}\Omega$ )	V <sub>OH</sub>	4.9	_	-	Vdc
Input Resistor	R1	15.4	22	28.6	kΩ
Resistor Ratio	R <sub>1</sub> /R <sub>2</sub>	0.38	0.47	0.56	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

# TYPICAL CHARACTERISTICS MUN2234, MMUN2234L, MUN5234, DTC124XE, DTC124XM3

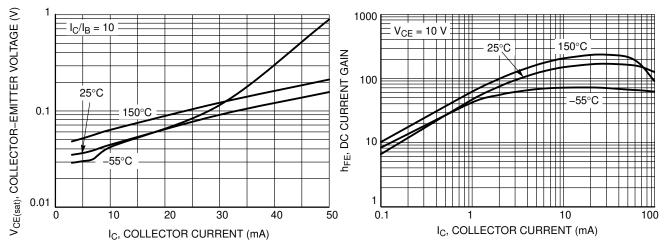


Figure 2. V<sub>CE(sat)</sub> vs. I<sub>C</sub>

Figure 3. DC Current Gain

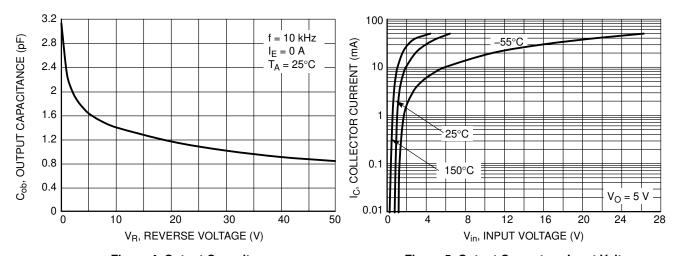


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

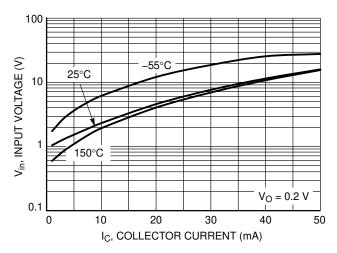
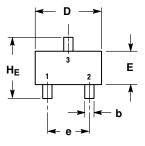
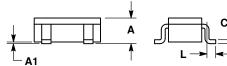


Figure 6. Input Voltage vs. Output Current

# **PACKAGE DIMENSIONS**

SC-59 CASE 318D-04 ISSUE H





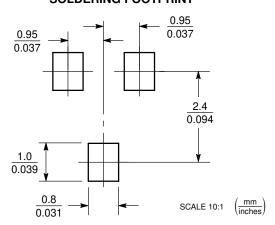
- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
С	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
е	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.80	3.00	0.099	0.110	0.118

STYLE 1: PIN 1. BASE

2. EMITTER 3. COLLECTOR

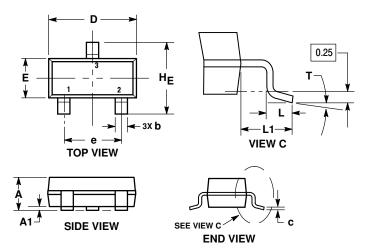
# **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# **PACKAGE DIMENSIONS**

SOT-23 (TO-236) CASE 318-08 **ISSUE AR** 



- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.

  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF
- THE BASE MATERIAL.

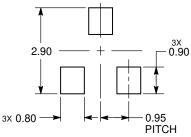
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
C	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Е	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
ΗE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

# STYLE 6: PIN 1. BASE

- EMITTER
   COLLECTOR

# **RECOMMENDED SOLDERING FOOTPRINT\***

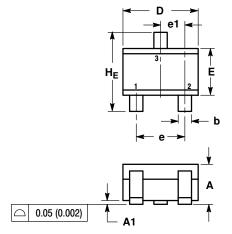


DIMENSIONS: MILLIMETERS

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# **PACKAGE DIMENSIONS**

## SC-70 (SOT-323) CASE 419-04 ISSUE N

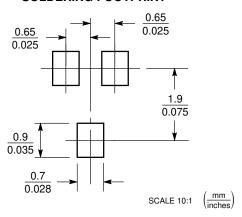


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 REF	
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1		0.65 BSC			0.026 BSC	;
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR

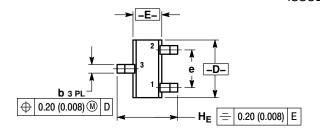
# **SOLDERING FOOTPRINT\***

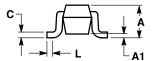


<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# **PACKAGE DIMENSIONS**

## SC-75/SOT-416 **CASE 463** ISSUE G



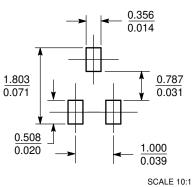


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.

	MIL	LIMETE	RS	INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
С	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.061	0.063	0.065
E	0.70	0.80	0.90	0.027	0.031	0.035
е	1	.00 BSC	)		0.04 BSC	
L	0.10	0.15	0.20	0.004	0.006	0.008
HF	1.50	1.60	1.70	0.060	0.063	0.067

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

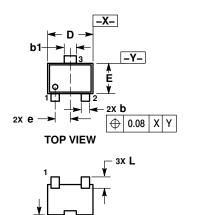
# **SOLDERING FOOTPRINT\***



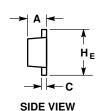
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### **PACKAGE DIMENSIONS**

### SOT-723 CASE 631AA ISSUE D



**BOTTOM VIEW** 



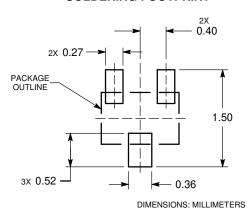
- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

  DIMENSIONS D AND E DO NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
Α	0.45	0.50	0.55
ь	0.15	0.21	0.27
b1	0.25	0.31	0.37
O	0.07	0.12	0.17
D	1.15	1.20	1.25
Е	0.75	0.80	0.85
е		0.40 BS0	)
ΗE	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

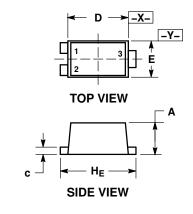
### **RECOMMENDED SOLDERING FOOTPRINT\***

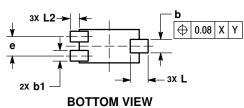


\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

SOT-1123 CASE 524AA ISSUE C





#### NOTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

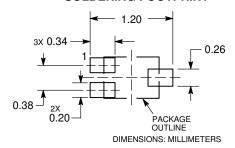
	MILLIMETERS		
ым	MIN	MAX	
Α	0.34	0.40	
b	0.15	0.28	
b1	0.10	0.20	
C	0.07	0.17	
D	0.75	0.85	
Е	0.55	0.65	
е	0.35	0.40	
HE	0.95	1.05	
L	0.185 REF		
L2	0.05	0.15	

STYLE 1:

PIN 1. BASE

2. EMITTER 3. COLLECTOR

### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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